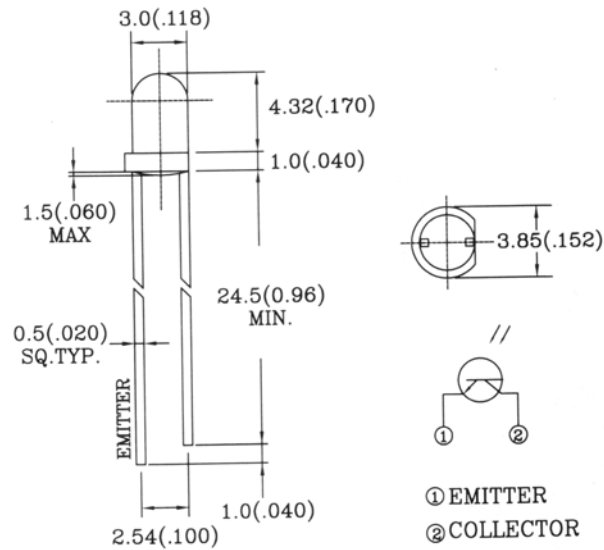
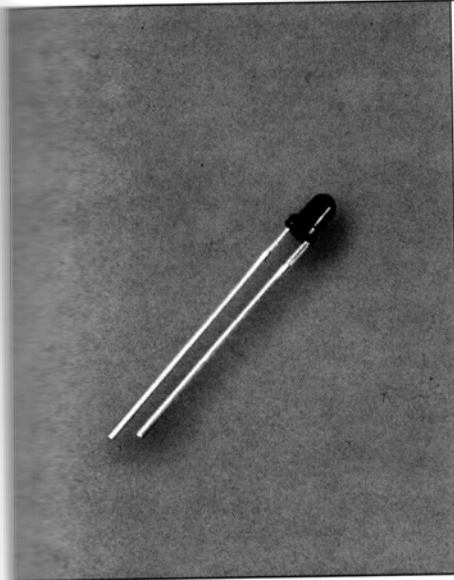


L-32XOPT1XX 3.0mm PHOTOTRANSISTOR



◆ABSOLUTE MAXIMUM RATING:(Ta=25°C)

Part No.	P _D (mw)	V _{(BR)R} (V)	T _{opr}	T _{stg}
L-32XOPT1XX	10	5	-35°C to 85°C	-35°C to 85°C
PARAMETER	Power Dissipation	Reverse Voltage	Operating Temperature Range	Storage Temperature Range
Lead Soldering Temperature {1.6mm(0.063 inch)From Body}250°C ±5°C For 3 Seconds				

◆ELECTRO-OPTICAL CHARACTERISTICS:(Ta=25°C)

Part No.	BV _{CEO} (V)			BV _{ECO} (V)			I _{CEO} (nA)			V _{CE} (s)(V)			t _r /t _f (uS)			I _c (mA)			Δλ (nm)			
	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
L-32ROPT1D1	30			5					100			0.4	15/15		0.2	0.6		900	940			
L-32AOPT1D1	30			5					100			0.4	15/15		0.6	1.0		900	940			
TEST CONDITION	I _C =100uA E _e =0mW/cm ²			I _E =100uA E _e =0mW/cm ²			V _E =20V E _e =0mW/cm ²			I _C =2mA E _e =0.5mW/cm ²			V _{CE} =5V I _C =1mA R _L =1000Ω			V _{CE} =5V E _e =0.1mW/cm ²						
PARAMETER	COLLECTOR-EMITTER BREAKDOWN VOLTAGE			EMITTER-COLLECTOR BREAKDOWN VOLTAGE			COLLECTOR DARK CURRENT			COLLECTOR-EMITTER SATURATION VOLTAGE			RISE/FALL TIME			ON STATE COLLECTOR CURRENT			SPECTRAL SENSITIVITY WAVELENGTH			

D1,D2=BLACK

1.All dimension are in millimeters(inches).

2.Tolerance is ±0.25mm(0.01")unless otherwise specified.